

# AlGaAs laser diodes

## RLD-78PP-B / RLD-78NP-D

The RLD-78PP-B and RLD-78NP-D are the world's first mass-produced laser diodes those are manufactured by molecular beam epitaxy. The characteristics of these laser diodes are suitable for laser beam printers.

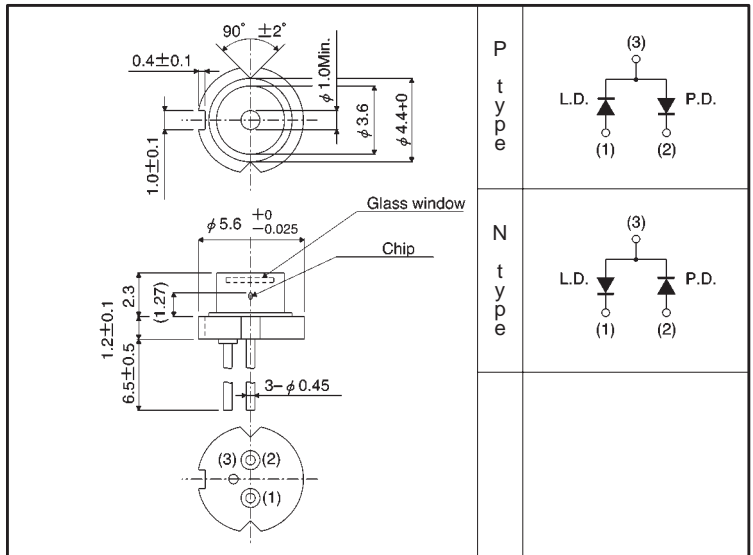
●Applications

Laser beam printers

●Features

- 1) One-third dispersion compared with conventional laser diodes.
- 2) High-precision, compact package.
- 3) Low droop.
- 4) Can be driven by single power supply.

●External dimensions (Units: mm)



●Absolute maximum ratings (Tc = 25°C)

| Parameter             |                | Symbol               | Limits  | Unit |
|-----------------------|----------------|----------------------|---------|------|
| Output                |                | Po                   | 5       | mW   |
| Reverse voltage       | Laser          | V <sub>R</sub>       | 2       | V    |
|                       | PIN photodiode | V <sub>R</sub> (PIN) | 30      | V    |
| Operating temperature |                | T <sub>opr</sub>     | -10~+60 | °C   |
| Storage temperature   |                | T <sub>stg</sub>     | -40~+85 | °C   |

●Electrical and optical characteristics (Tc = 25°C)

| Parameter                      | Symbol                                 | Min. | Typ. | Max.     | Unit    | Conditions                  |
|--------------------------------|--|------|------|----------|---------|-----------------------------|
| Threshold current              | $I_{th}$                               | 15   | 25   | 45       | mA      | —                           |
| Operating current              | $I_{op}$                               | 25   | 45   | 65       | mA      | Po=3mW                      |
| Operating voltage              | $V_{op}$                               | —    | 1.9  | 2.3      | V       | Po=3mW                      |
| Differential efficiency        | $\eta$                                 | 0.1  | 0.2  | 0.3      | mW/mA   | $\frac{2mW}{I(3mW)-I(1mW)}$ |
| Monitor current                | $I_m$                                  | 0.3  | 0.55 | 0.9      | mA      | Po=3mW                      |
| Parallel divergence angle      | $\theta_{//}^*$                        | 8    | 11   | 15       | deg     | Po=3mW                      |
| Perpendicular divergence angle | $\theta_{\perp}^*$                     | 25   | 30   | 38       | deg     |                             |
| Parallel deviation angle       | $\Delta\phi_{//}$                      | —    | —    | $\pm 2$  | deg     |                             |
| Perpendicular deviation angle  | $\Delta\phi_{\perp}$                   | —    | —    | $\pm 3$  | deg     |                             |
| Emission point accuracy        | $\Delta X$<br>$\Delta Y$<br>$\Delta Z$ | —    | —    | $\pm 80$ | $\mu m$ | —                           |
| Peak emission wavelength       | $\lambda$                              | 770  | 785  | 795      | nm      | Po=3mW                      |
| Droop                          | $\Delta P$                             | —    | 5    | 10       | %       | Po=3mW                      |

\*  $\theta_{//}$  and  $\theta_{\perp}$  are defined as the angle within which the intensity is 50% of the peak value.

●Electrical and optical characteristic curves

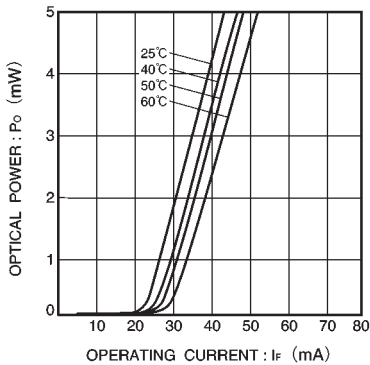


Fig. 1 Optical output vs. operating current

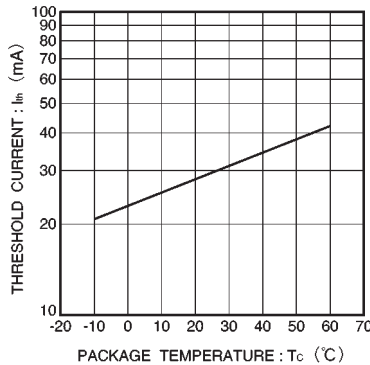


Fig. 2 Dependence of threshold current on temperature

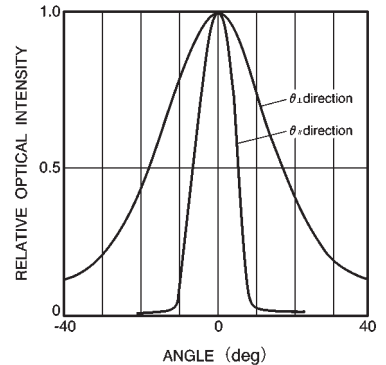


Fig. 3 Far field pattern

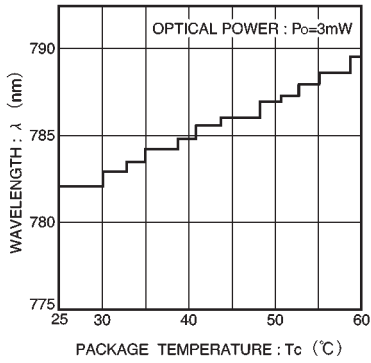


Fig. 4 Dependence of wavelength on temperature

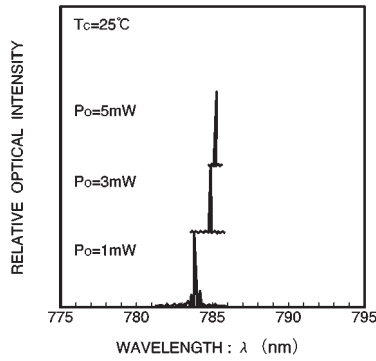


Fig. 5 Dependence of emission spectrum on optical output

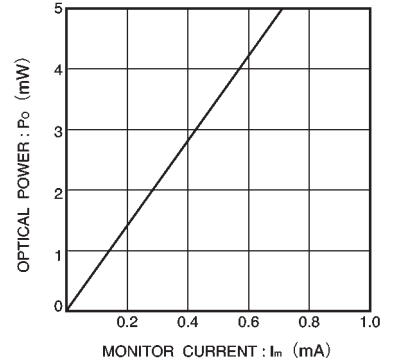


Fig. 6 Monitor current vs. optical output

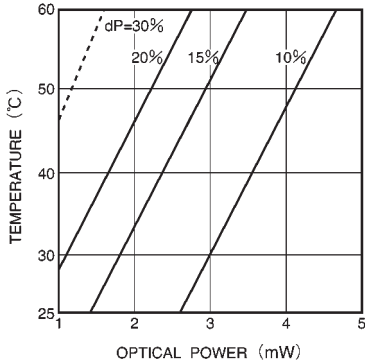


Fig. 7 Temperature vs. output guidelines for various droop percentages

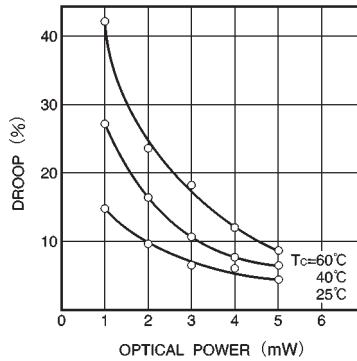


Fig. 8 Dependence of droop on output and temperature